



2N7002

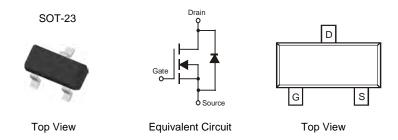
N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



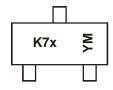
Ordering Information (Note 3)

Part Number	Case	Packaging
2N7002-7-F	SOT-23	3000/Tape & Reel

Notes:

- 1. No purposefully added lead. Halogen and Antimony Free.
 - 2. Product manufactured with Date Code V12 (week 50, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V12 are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.
 - 3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



K7x = Product Type Marking Code, e.g. K72 YM = Date Code Marking Y = Year (ex: N = 2002)

M = Month (ex: 9 = September)

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	M	N	Р	R	S	Т	U	V	W	Х	Υ	Z
Month	Jan	Fe	b I	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Oc	t	Nov	Dec
Code	1	2		3	4	5	6		7	8	9	0		N	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characte	Symbol	Value	Units	
Drain-Source Voltage	V_{DSS}	60	V	
Drain-Gate Voltage R _{GS} ≤ 1.0MΩ		V_{DGR}	60	V
Gate-Source Voltage	Continuous Pulsed	V_{GSS}	±20 ±40	V
Drain Current (Note 4)	Continuous Continuous @ 100°C Pulsed	I _D	115 73 800	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	D	300	mW
Derating above T _A = 25°C	P_{D}	2.4	mW/°C
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	T_{J}, T_{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

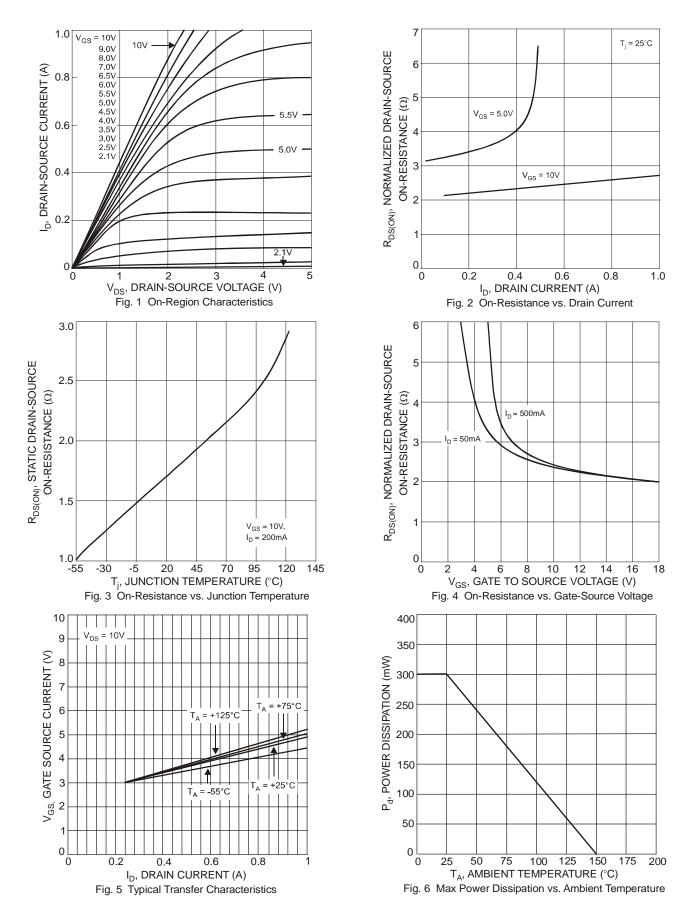
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage		BV _{DSS}	60	70	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ $T_C = 25^{\circ}C$ @ $T_C = 125^{\circ}C$	I _{DSS}		_	1.0 500	μΑ	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage		I _{GSS}		_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage		$V_{GS(th)}$	1.0	_	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	@ T _J = 25°C @ T _J = 125°C	R _{DS} (ON)	_	3.2 4.4	7.5 13.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$ $V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current		I _{D(ON)}	0.5	1.0	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance		g FS	80	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage (Note 6)		V_{SD}	_	0.78	1.5	V	$V_{GS} = 0V, I_S = 115mA$
Continuous Source Current (Note 6)		Is		_	200	mA	_
Pulse Source Current (Note 6)		I _{SD}		_	2	Α	_
DYNAMIC CHARACTERISTICS							
Input Capacitance		Ciss		22	50	pF)/ 05)/)/ 0)/
Output Capacitance		Coss		11	25	pF	$V_{DS} = 25V, V_{GS} = 0V$ of = 1.0MHz
Reverse Transfer Capacitance		Crss		2.0	5.0	pF	1 = 1.0101112
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		t _{D(ON)}	_	7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time		t _{D(OFF)}	_	11	20	ns	$\begin{aligned} R_{L} &= 150\Omega, \ V_{GEN} = 10V, \\ R_{GEN} &= 25\Omega \end{aligned}$

Notes:

- 4. Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at http://www.diodes.com/datashaots/pp02001.pdf
- website at http://www.diodes.com/datasheets/ap02001.pdf.

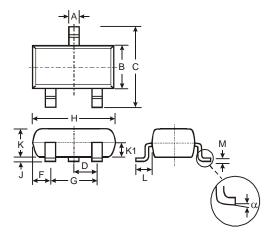
 5. Short duration pulse test used to minimize self-heating effect.
- 6. V_{SD} measured in 250 μ s pulse, duty cycle = 2%; I_{SD} measure in 10ms Repetitive Pulse, duty cycle = 2%, Pd_Pulse is from Zth test data





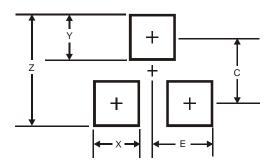


Package Outline Dimensions



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.903	1.10	1.00					
K1	-	-	0.400					
L	0.45	0.61	0.55					
М	0.085	0.18	0.11					
α	0°	8°	-					
All Dimensions in mm								

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35



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